



JMT200KT18T2C



Electrical Characteristics (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Conditions | Symbol | Values | | | Unit |
|----------------------|---------------------------------------|--------|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| Peak forward voltage | $I_T=600\text{A}, t_P=380\mu\text{s}$ | V_T | | | 1.80 | V |

$$V_D = V_{\text{DRM}}, T = V$$

Repetitive peak off-state current



Ordering Information

| Device | Marking | Package | Weight | Inner Box | Pre Carton |
|---------------|---------------|---------|-------------|-----------|------------|
| JMT200KT18T2C | JMT200KT18T2C | T2 | 170±10g/PCS | 6 PCS | 72 PCS |

Typical Electrical & Thermal Characteristics

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

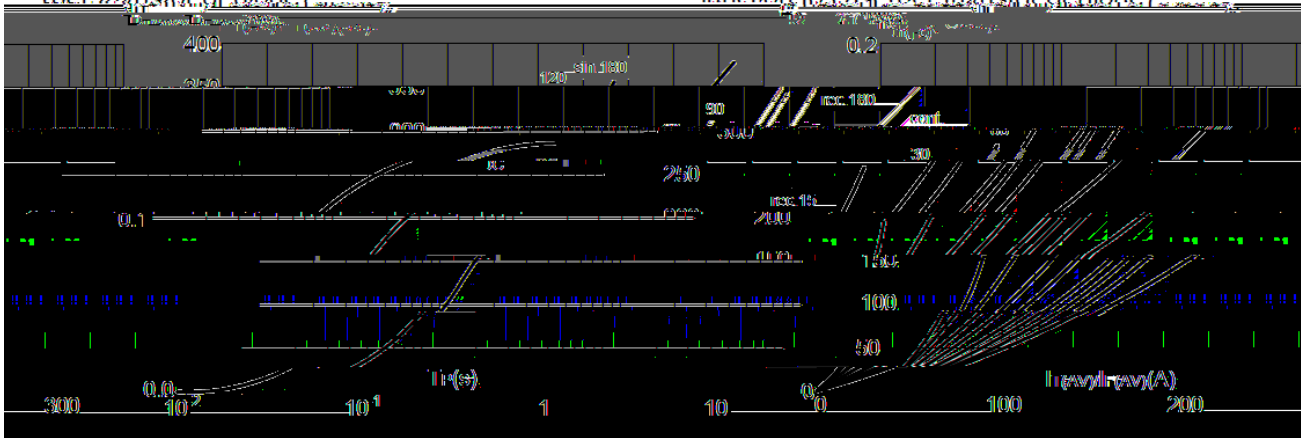
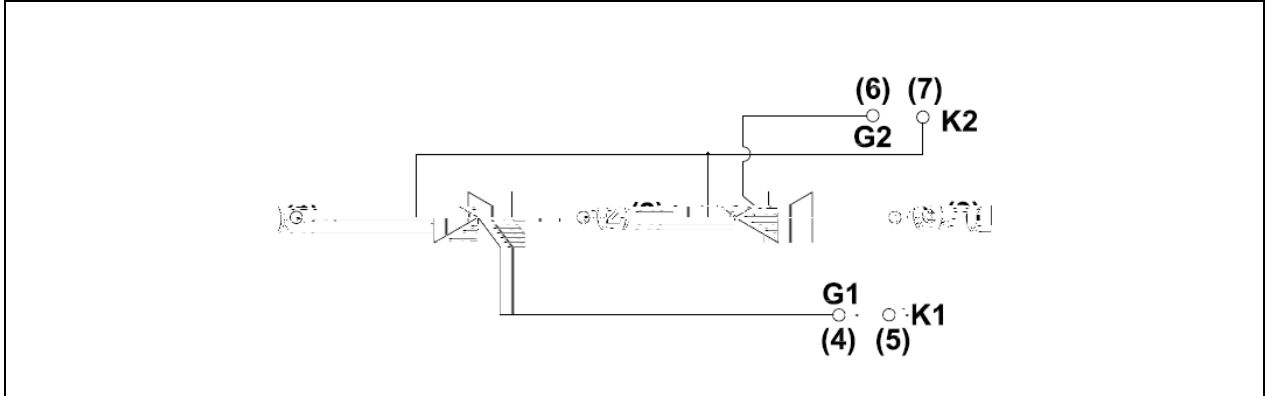


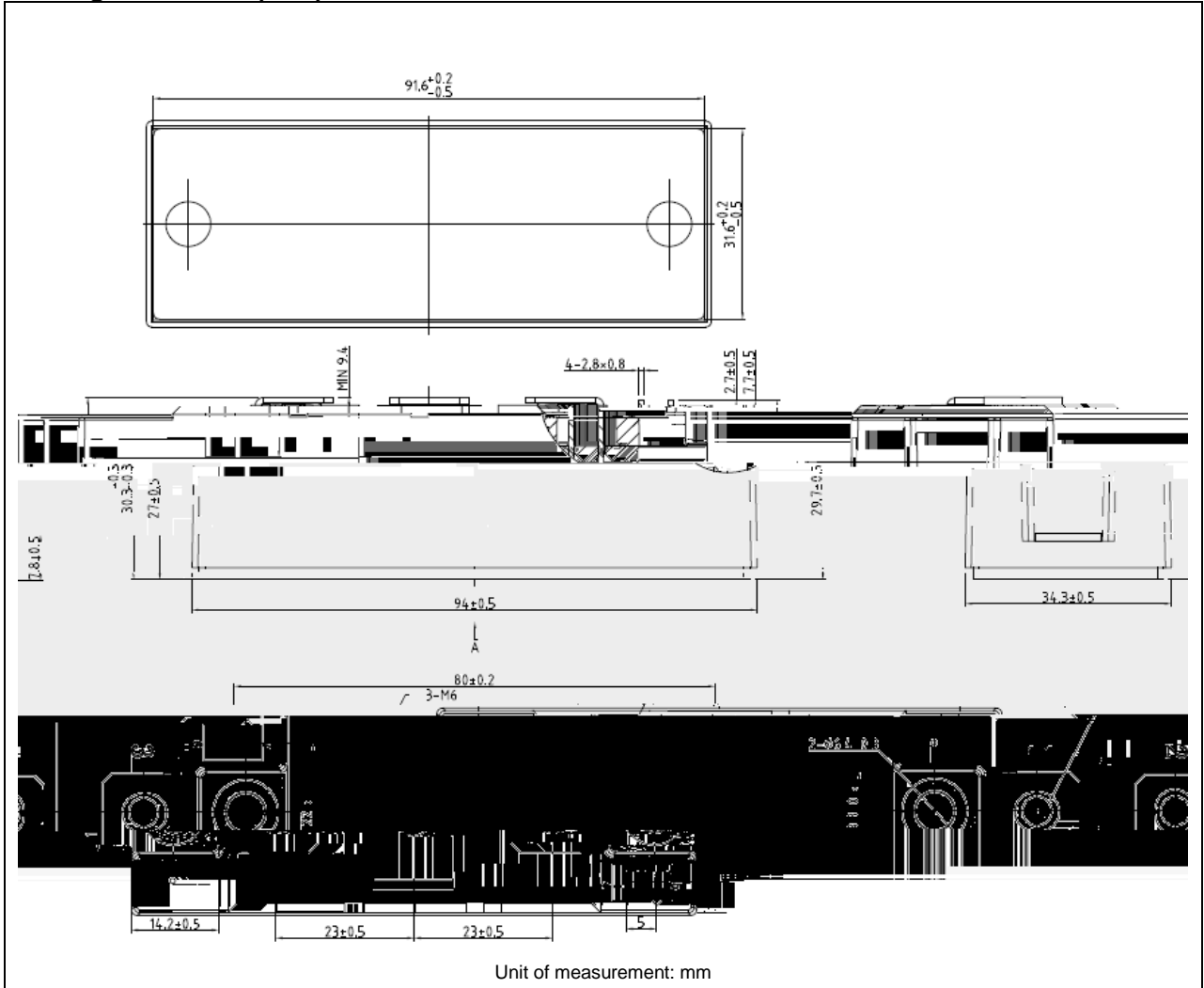
FIG.2: Maximum transient thermal impedance junction to case (per thyristor or diode)



Circuit Diagram



Package Outlines (mm)





Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Semiconductor Co., Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. This information in this document is subject to change without prior notice. Notwithstanding this, Jiangsu JieJie will fully comply with the terms outlined in a signed agreement. Products and information provided in this